Supplementary Information

for

Surface grafting of octylamine onto poly(ethylene-*alt*-maleic anhydride) gate insulators for low-voltage DNTT thin-film transistors

Yun-Seo Choe,[ab] Mi Hye Yi,[a] Ji-Heung Kim,[b] Yun Ho Kim,*[a] and Kwang-Suk Jang*[a]

[a]*Division of Advanced Materials, Korea Research Institute of Chemical Technology, Daejeon 34114, Republic of Korea. E-mail: kjang@krict.re.kr, yunho@krict.re.kr*

[b]*School of Chemical Engineering, Sungkyunkwan University, Suwon 16419, Republic of Korea*

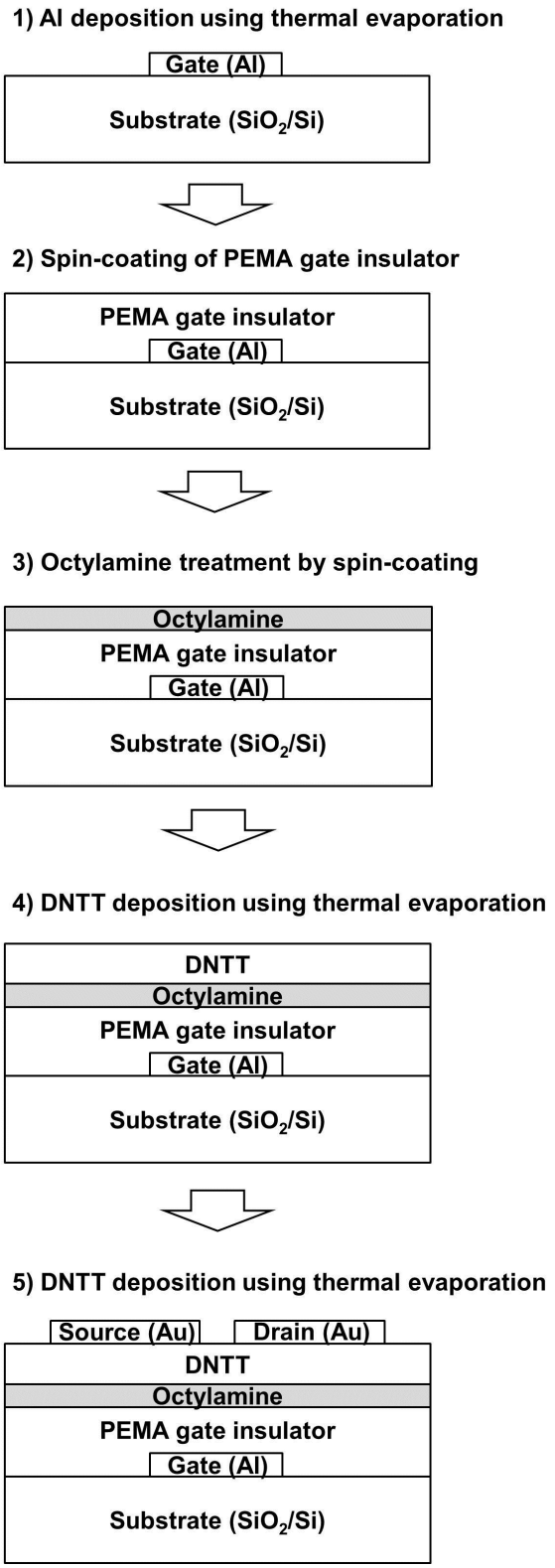
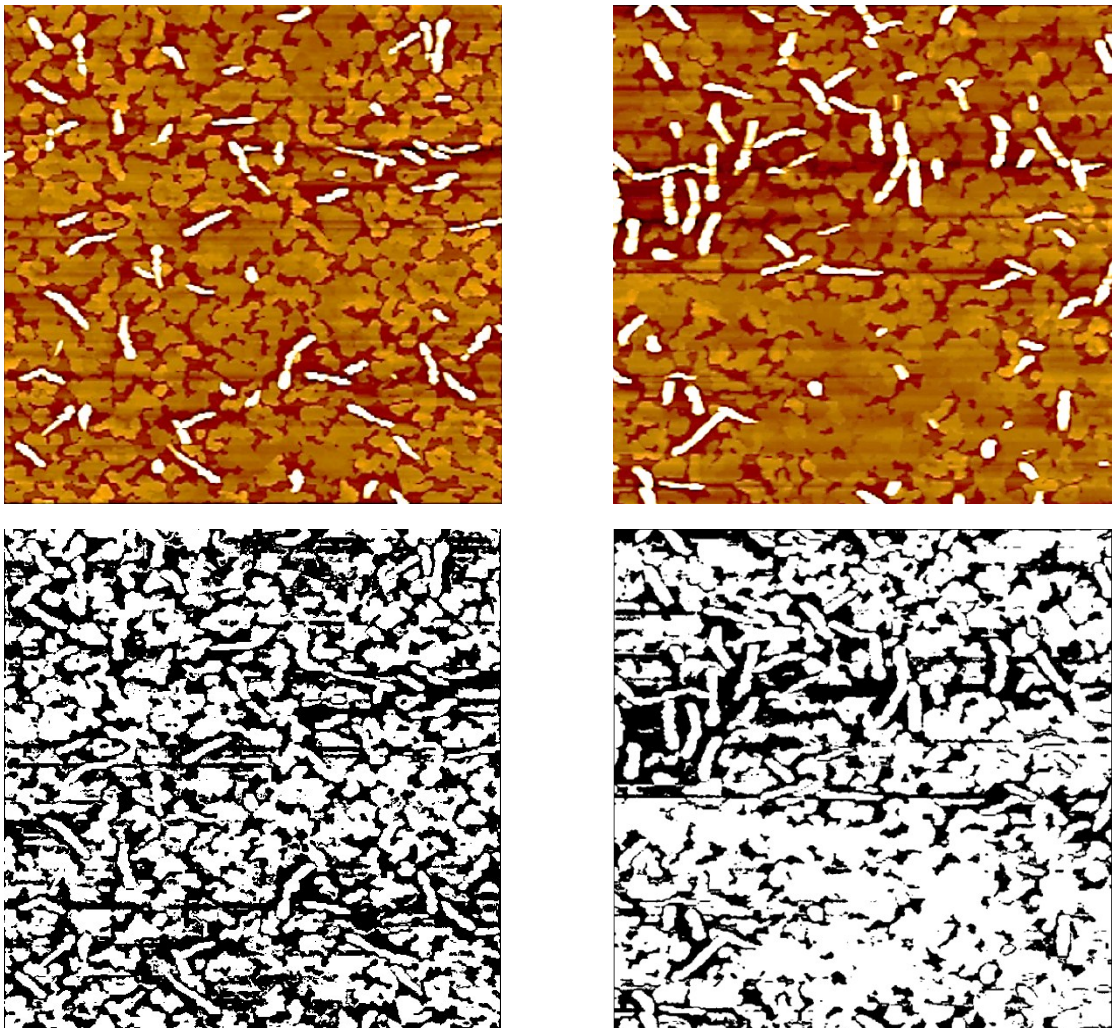


Fig. S1 Scheme of the TFT device fabrication.

non-treated **octylamine-treated**



→ 100 – 49.544 = 50.467 µm² **→ 100 – 30.711 = 69.289 µm²**

Results

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	Area	Mean	Min	Max	MinThr	MaxThr
1	49.533	255	255	255	9	255
2	30.711	255	255	255	255	255

Fig. S2 The surface coverage measurement of the 12 nm-thick DNTT layers on non-treated and octylamine-treated PEMA thin films.

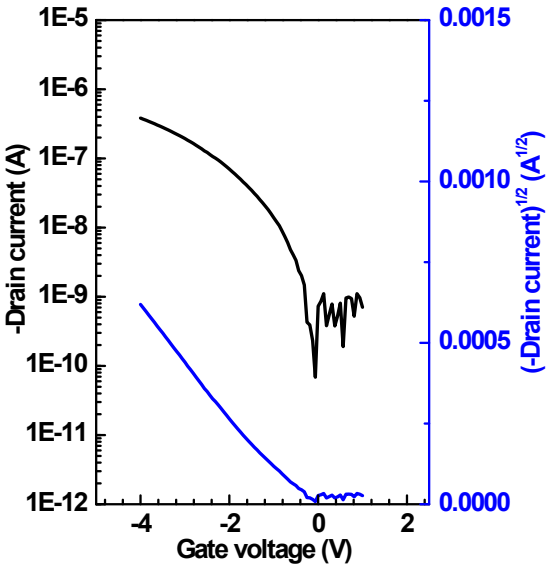

Fig. S3 Transfer characteristic (I_{ds} vs. V_{gs}) of the DNTT TFTs with the 60 nm-thick SiO_2 gate insulator.